

Abstract of the Disclosure:

In a reflection type mask blank for EUV exposure with a substrate, a multilayer film is formed on the substrate so as to reflect an EUV light ray. A light absorber layer is formed on the multilayer film so as to absorb the EUV light ray. The multilayer film has flatness with respect to a surface thereof, and the flatness is 100 nm or less.

T09T4 06628660